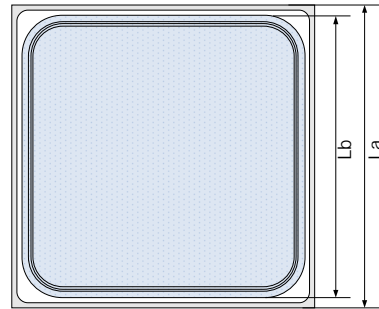


**2SB108060ML SCHOTTKY BARRIER DIODE CHIPS**
**DESCRIPTION**

- Ø 2SB108060ML is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Ø Chip Size:1080 $\mu$ m X 1080 $\mu$ m;
- Ø Chip Thickness: 280 $\pm$ 20 $\mu$ m;


**Chip Topography and Dimensions**

 La: Chip Size: 1080 $\mu$ m;

 Lb: Pad Size: 985 $\mu$ m;

**ORDERING SPECIFICATIONS**

Product Name	Specification
2SB108060MLYY	For axial leads package

**ABSOLUTE MAXIMUM RATINGS**

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	60	V
Average Forward Rectified Current	IFAV	2	A
Peak Forward Surge Current@8.3ms	IFSM	50	A
Maximum Operation Junction Temperature	TJ	125	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~125	$^{\circ}$ C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25 $^{\circ}$ C)**

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=1mA	60	--	V
Forward Voltage	VF	IF=2A	--	0.70	V
Reverse Current	IR	VR=60V	--	1	mA